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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

J-1 J-1	Ritu Tyagi, et. al., "An Isoplanar Isolation Technology for SiC Devices Using Local Oxidation" J. Electrochem. Soc., Vol. 141, No. 8, August 1994.
	N. Kiritani, et al., Nissan Motor CO., LTD. Nissan Research Center, Electronics and Information Systems Research Laboratory, "Thermal oxide growth on 4H-SiC using H ₂ O direct oxidation" The Japan Society of Applied Physics and Related Societies, The 47th Spring Meeting, Extended Abstracts, March 28, 2000 (English Abstract).
EXAMINER F. J. ...	DATE CONSIDERED 10/25/2002

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.